

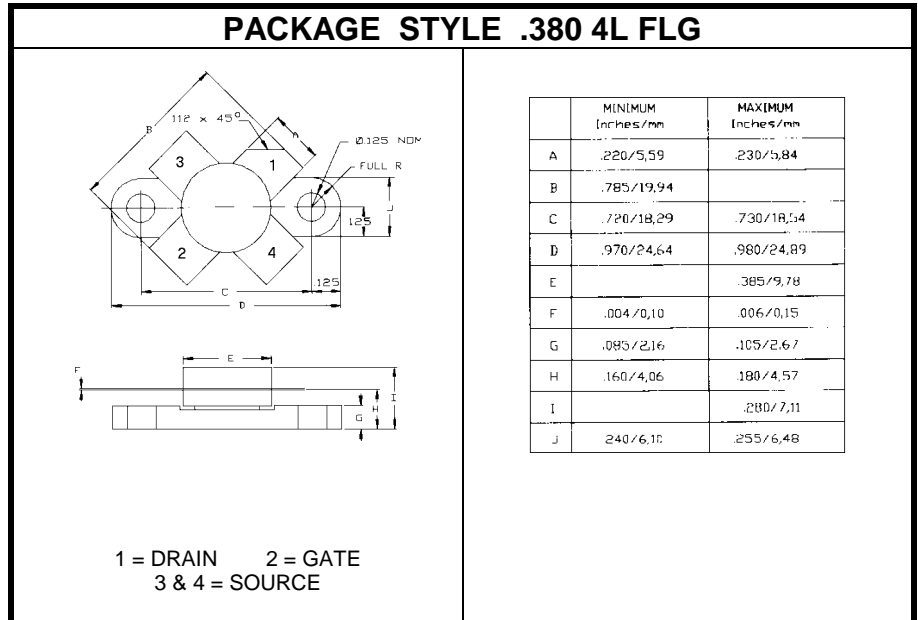
RF POWER FIELD-EFFECT TRANSISTOR

DESCRIPTION:

The **ASI MRF136** is a N-Channel Enhancement MOSFET, Designed for Wideband Large Signal Amplifier Applications up to 400 MHz.

MAXIMUM RATINGS

I_D	2.5 A
V_{DSS}	65 V
P_{DISS}	50 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	3.6 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{(BR)DSS}	I _D = 5.0 mA	V _{GS} = 0 V		65			V
I_{DSS}	V _{DS} = 28 V	V _{GS} = 0 V				2.0	mA
I_{GSS}	V _{DS} = 0 V	V _{GS} = 40 V				1.0	μA
V_{GS(th)}	I _D = 25 mA	V _{DS} = 10 V		1.0	3.0	6.0	V
g_{fs}	I _D = 250 mA	V _{DS} = 10 V		250	400		mmhos
C_{iss} C_{oss} C_{rss}	V _{DS} = 28 V	V _{GS} = 0 V	f = 1.0 MHz		24	25	pF
NF	V _{DS} = 28 V	I _D = 0.5 A	f = 150 MHz		1.0		dB
G_{ps} η	V _{DD} = 28 V I _{DQ} = 25 mA	P _{out} = 15 W	f = 150 MHz	12 50	16 60		dB %
ψ	V _{DD} = 28 V I _{DQ} = 25 mA	P _{out} = 15 W VSWR 30:1 @ ALL PHASE ANGLES	f = 150 MHz	NO DEGRADATION IN OUTPUT POWER			